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(54) **SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD OF THE SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

There are provided a semiconductor device and a manufacturing method thereof. The semiconductor device includes: a stack structure; a source structure; a channel structure penetrating the stack structure, the channel structure being connected to the source structure; and a first memory layer interposed between the channel structure and the stack structure. The source structure includes a first protrusion part protruding between the first memory layer and the channel structure.